## IN THE CLAIMS

Claims 1-33 (cancelled).

- 34. (currently amended) An intermediary of a semiconductor device comprising:
- a semiconductor substrate formed with a first recessed region having a lower surface depressed with respect to a major surface of the semiconductor substrate;
- a pillar region comprised of a plurality of pillars comprising a dielectric material formed in the first recessed region and extending from the lower surface of the first recessed surface, wherein a plurality of voids is within the pillar region; and
- a <u>plurality</u> of polysilicon cap layers having a <u>lower</u> surface formed adjoining <del>upper surfaces of the pillar region</del> and overlying each of the plurality of pillars, wherein the <u>lower</u> surface of the <u>plurality of polysilicon</u> cap layers is aligned with <u>a top surface of each of the plurality of voids</u>, and wherein sidewall surfaces of the plurality of pillars are devoid of the polysilicon cap layers, and wherein the pillar region and the <u>plurality of polysilicon cap layers</u> are configured to form an isolation region having reduced substrate capacitance.
- 35. (currently amended) The intermediary of claim 34, wherein <u>each of the plurality of polysilicon cap layers</u> has a thickness of about 4,500 angstroms.
- 36. (previously presented) The intermediary of claim 34, wherein the upper surfaces of the pillar region are

recessed below the major surface of the semiconductor substrate.

- 37. (previously presented) The intermediary of claim 36, wherein the upper surfaces are recessed a distance of about 0.5 microns.
- 38. (previously presented) The intermediary of claim 34, wherein the pillar region comprises deposited silicon dioxide.
- 39. (previously presented) The intermediary of claim 34, wherein the pillar region comprises a matrix of a plurality of pillars.
- 40. (currently amended) The intermediary of claim 39, wherein at least a portion of the matrix of <u>a plurality of</u> pillars includes pillars having a generally rectangular shape.
  - 41. Cancelled.
- 42. (previously presented) The intermediary of claim 34, wherein the pillar region extends a distance of about 4.5 micrometers from the lower surface of the first recessed region and has a dielectric constant of about 3.5.